AMENDMENTS TO THE CLAIMS

Set forth below is a listing of the claims of the instant Application. Claims 1-9 are canceled and replaced with new Claims 10-21. Please enter of record for the instant Application the claims as listed herein.

Claims 1-9 (canceled).

3

Claim N (new): A method for measuring growth parameters of a multi-layer material while the layers are being built up comprising the steps of illuminating a layer during epitaxy under constant processing conditions with a constant illuminating energy and measuring the reflectivity of the layer over time to determine a position and a value of an extremum of Fabry-Perot oscillations of the layer and then comparing the position and the value of the extremum to a standard.

Claim (new): The method of claim (wherein the multi-layer material is a semiconductor.

Claim 12 (new): The method of claim 10 wherein the position and the value of a first minimum of the Fabry-Perot oscillations is utilized.

Claim 13 (new): The method of claim 10 wherein the growth parameters are process temperature, growth rate, composition or concentration of incorporated doping materials.

Claim (new): The method of claim (new): The meth

Claim 16 (new): The method of claim 14, wherein the measured reflectivity is normalized.

- Claim 16 (new): The method of claim 10, wherein at the end of a process step or of the whole process, a layer of the same material as a substrate material, on which at least one layer is built up, is washed and its characteristics are compared with the characteristics present at the start of the process.
- Claim \(\frac{1}{2} \) (new): The method of claim \(\frac{1}{2} \), wherein the material properties are monitored at the same time, at least before the start and after the end of the process by an RAS measurement.
- Claim 18 (new): The method of claim 10, wherein the reflectivity at the position and the value of the extremum of the Fabry-Perot oscillations under consideration is used to determine the process temperature.
- Claim \Re (new): The method of claim \Re , wherein the process time up to the position and the value of the extremum of the Fabry-Perot oscillations under consideration is used to determine the growth rate of the layers.
- Claim 20 (new): The method of claim 10, wherein, when the process temperature is determined previously, a position and a value of an extremum of Fabry-Perot oscillations of a ternary layer under consideration is used to determine the composition of the layer.
- Claim 2 (new): The method of claim 10, wherein the illumination energy is selected in a range, in which the temperature dependence of a real part of a dielectric function of participating materials is monotonic.